# SILICON EPITAXIAL PLANAR DIODE

# **Band Swithing Diode**

#### **Features**

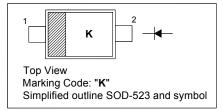
- Extremely small surface mounting type
- High reliability

## **Applications**

• High frequency switching

#### **PINNING**

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	35	V
Forward Current	I <sub>F</sub>	100	mA
Junction Temperature	T <sub>J</sub>	125	°C
Storage Temperature Range	T <sub>stg</sub>	- 55 to + 125	°C

# Characteristics at $T_a = 25$ °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I <sub>F</sub> = 10 mA	V <sub>F</sub>	1	V
Reverse Current at $V_R = 25 \text{ V}$	I <sub>R</sub>	10	nA
Capacitance Between Terminals at $V_R = 6 \text{ V}$ , $f = 1 \text{ MHz}$	Ст	1.2	pF
Forward Operating Resistance at I <sub>F</sub> = 2 mA, f = 100 MHz	R <sub>F</sub>	0.7	Ω







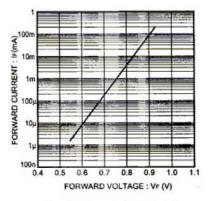


Fig. 1 Forward characteristics

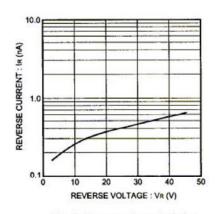


Fig. 2 Reverse characteristics

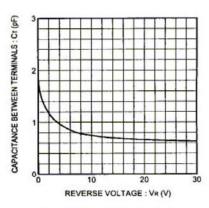


Fig. 3 Capacitance between terminals characteristics

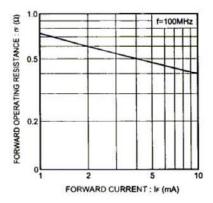


Fig. 4 Forward operating resistance characteristics









## **PACKAGE OUTLINE**

## Plastic surface mounted package; 2 leads

**SOD-523** 

